

30 V, 3 A, Low $V_{CE(sat)}$ NPN Transistor

NSS30201MR6T1G, SNSS30201MR6T1G

onsemi's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical application are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

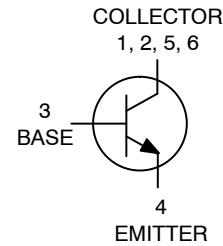
Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These are Pb-Free Devices*

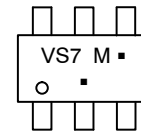
30 VOLTS
 3.0 AMPS
 NPN LOW $V_{CE(sat)}$ TRANSISTOR
 EQUIVALENT $R_{DS(on)}$ 100 m Ω



TSOP-6
 CASE 318G
 STYLE 6



DEVICE MARKING



VS7 = Specific Device Code
 M = Date Code
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NSS30201MR6T1G	TSOP-6 (Pb-Free)	3,000 / Tape & Reel
SNSS30201MR6T1G	TSOP-6 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	30	V
Collector-Base Voltage	V _{CBO}	50	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current – Continuous	I _C	2.0	A
Collector Current – Peak	I _{CM}	3.0	A

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D (Note 1)	535 4.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 1)	234	°C/W
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D (Note 2)	1,180 9.4	W mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 2)	106	°C/W
Thermal Resistance, Junction-to-Lead #1	R _{θJL} (Note 1) R _{θJL} (Note 2)	110 50	°C/W °C/W
Total Device Dissipation (Single Pulse < 10 s)	P _{Dsingle} (Notes 2 and 3)	1.75	W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 with 1 oz and 3.9 mm² of copper area.
2. FR-4 with 1 oz and 645 mm² of copper area.
3. Refer to Figure 8.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage ($I_C = 10\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	30	–	–	V
Collector – Base Breakdown Voltage ($I_C = 0.1\text{ mA}$, $I_E = 0$)	$V_{(BR)CBO}$	50	–	–	V
Emitter – Base Breakdown Voltage ($I_E = 0.1\text{ mA}$, $I_C = 0$)	$V_{(BR)EBO}$	5.0	–	–	V
Collector Cutoff Current ($V_{CB} = 30\text{ V}$, $I_E = 0$)	I_{CBO}	–	–	0.1	μA
Collector – Emitter Cutoff Current ($V_{CES} = 30\text{ V}$)	I_{CES}	–	–	0.1	μA
Emitter Cutoff Current ($V_{EB} = 4.0\text{ V}$)	I_{EBO}	–	–	0.1	μA
ON CHARACTERISTICS					
DC Current Gain (Note 4) ($I_C = 1.0\text{ mA}$, $V_{CE} = 5.0\text{ V}$) ($I_C = 0.5\text{ A}$, $V_{CE} = 5.0\text{ V}$) ($I_C = 1.0\text{ A}$, $V_{CE} = 5.0\text{ V}$)	h_{FE}	300 300 200	– 500 –	– 900 –	
Collector – Emitter Saturation Voltage (Note 4) ($I_C = 1.0\text{ A}$, $I_B = 100\text{ mA}$) ($I_C = 0.5\text{ A}$, $I_B = 50\text{ mA}$) ($I_C = 0.1\text{ A}$, $I_B = 1.0\text{ mA}$)	$V_{CE(sat)}$	– – –	0.10 0.06 0.05	0.200 0.125 0.075	V
Base – Emitter Saturation Voltage (Note 4) ($I_C = 1.0\text{ A}$, $I_B = 0.1\text{ A}$)	$V_{BE(sat)}$	–	–	1.1	V
Base – Emitter Turn-on Voltage (Note 4) ($I_C = 1.0\text{ A}$, $V_{CE} = 2.0\text{ V}$)	$V_{BE(on)}$	–	–	1.1	V
Cutoff Frequency ($I_C = 100\text{ mA}$, $V_{CE} = 5.0\text{ V}$, $f = 100\text{ MHz}$)	f_T	200	300	–	MHz
Output Capacitance ($f = 1.0\text{ MHz}$)	C_{obo}	–	–	15	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulsed Condition: Pulse Width $\leq 300\ \mu\text{sec}$, Duty Cycle $\leq 2\%$.

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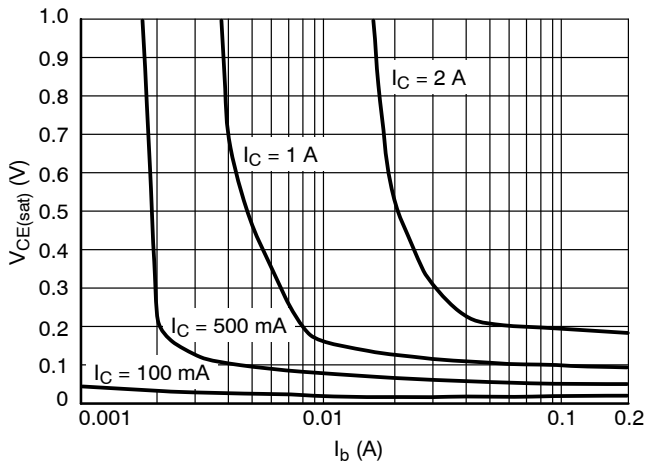


Figure 1. $V_{CE(sat)}$ versus I_b

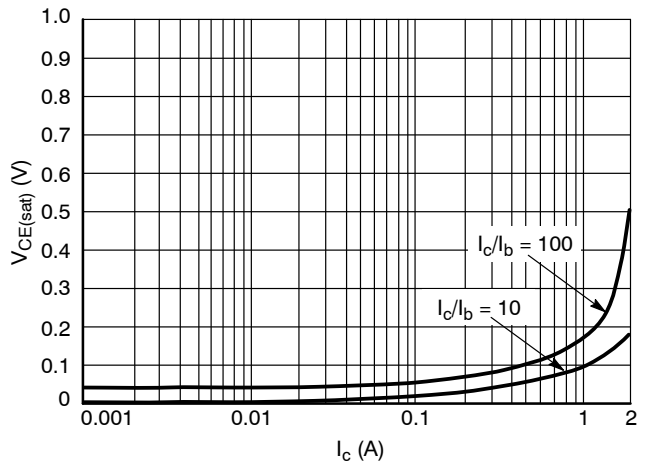


Figure 2. $V_{CE(sat)}$ versus I_c

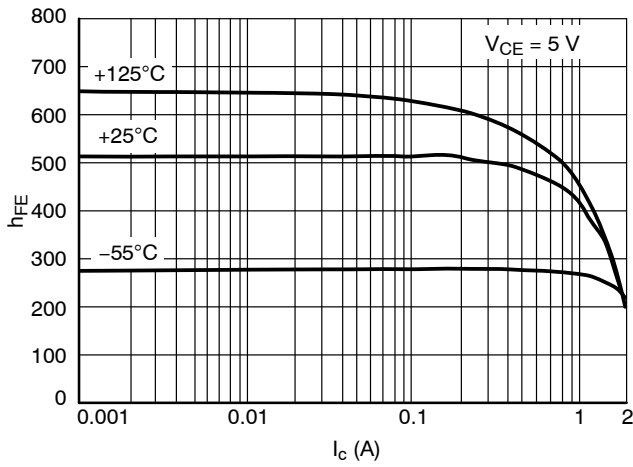


Figure 3. h_{FE} versus I_c

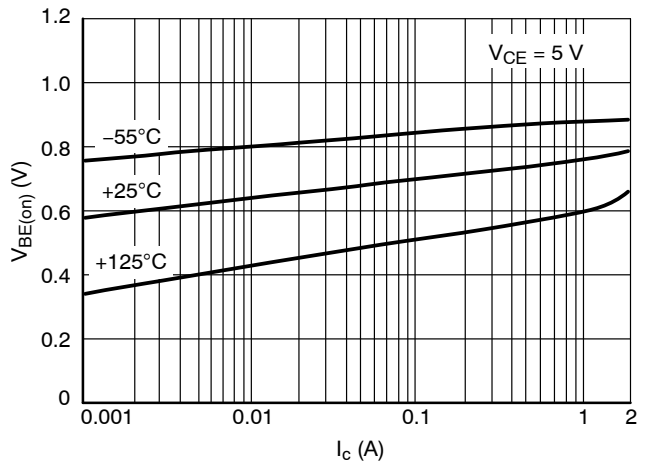


Figure 4. $V_{BE(on)}$ versus I_c

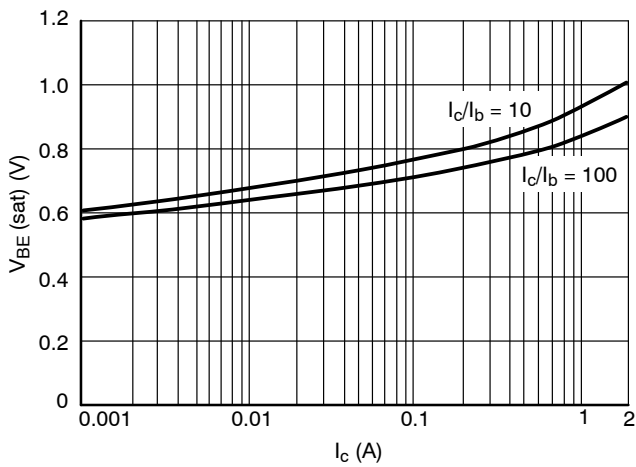


Figure 5. $V_{BE(sat)}$ versus I_c

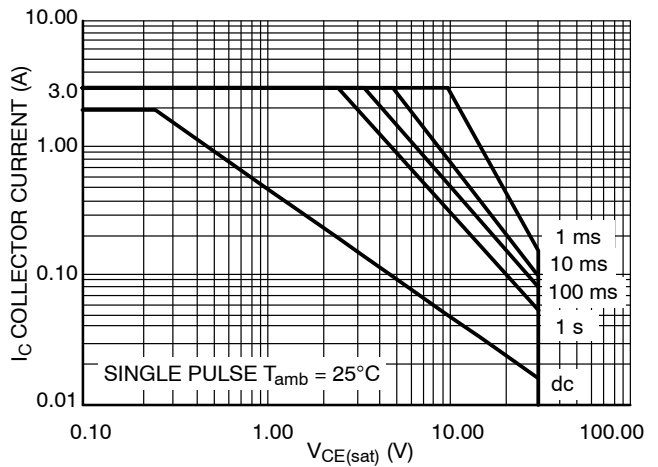


Figure 6. Safe Operating Area

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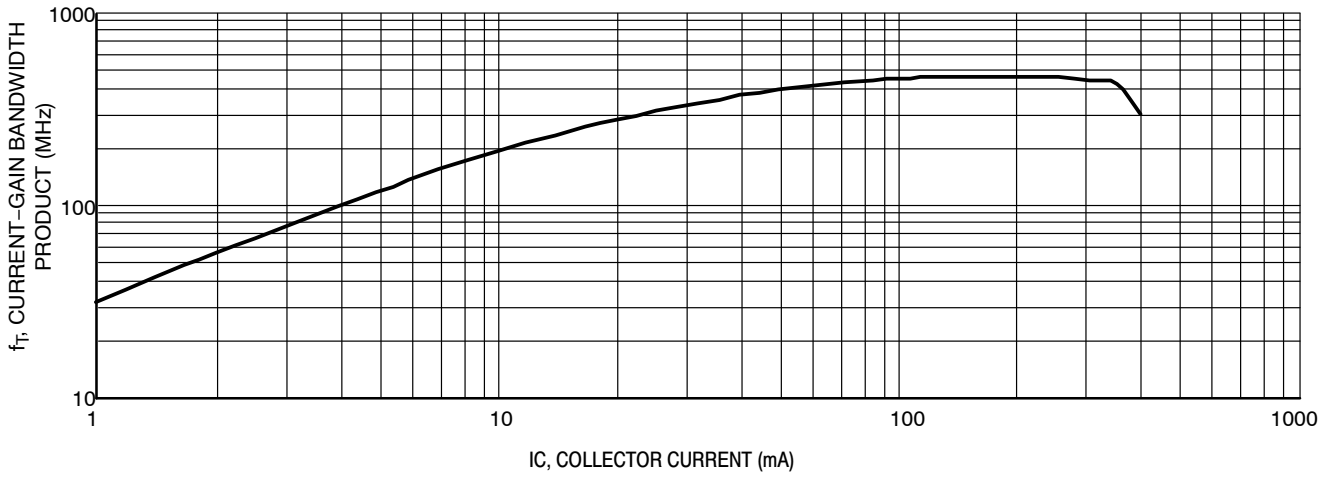


Figure 7. f_T (MHz) versus I_C (mA)
 $V_{CE} = 5.0$ V

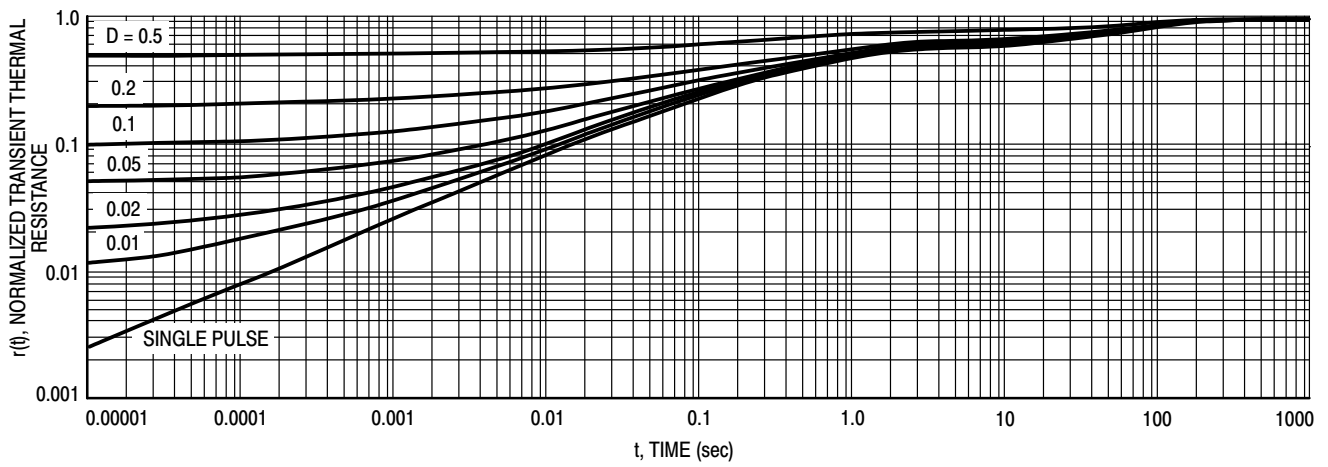
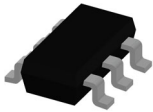
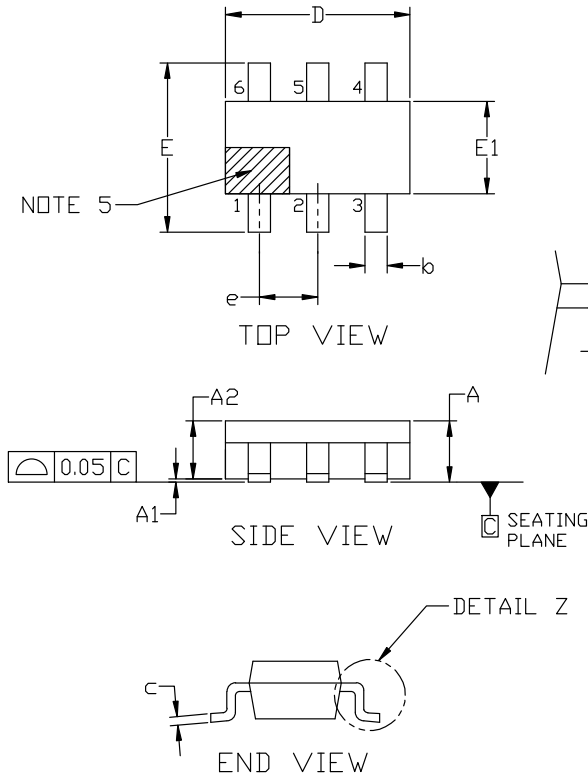


Figure 8. Normalized Thermal Response



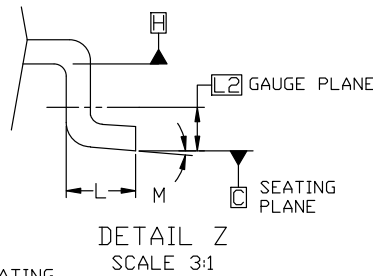
TSOP-6 3.00x1.50x0.90, 0.95P
CASE 318G
ISSUE W

DATE 26 FEB 2024

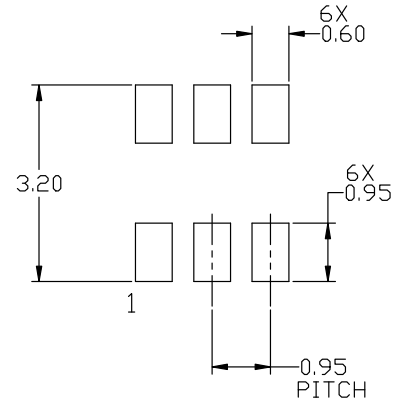


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN 1 INDICATOR MUST BE LOCATED IN THE INDICATED ZONE



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
A2	0.80	0.90	1.00
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
M	0°	---	10°



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

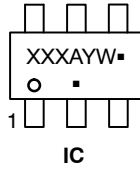
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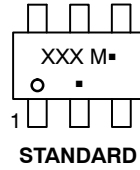
TSOP-6 3.00x1.50x0.90, 0.95P
CASE 318G
ISSUE W

DATE 26 FEB 2024

**GENERIC
MARKING DIAGRAM***



IC



STANDARD

XXX = Specific Device Code	XXX = Specific Device Code
A = Assembly Location	M = Date Code
Y = Year	▪ = Pb-Free Package
W = Work Week	
▪ = Pb-Free Package	

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

- | | | | | | |
|---|---|--|--|--|---|
| <p>STYLE 1:
 PIN 1. DRAIN
 2. DRAIN
 3. GATE
 4. SOURCE
 5. DRAIN
 6. DRAIN</p> | <p>STYLE 2:
 PIN 1. EMITTER 2
 2. BASE 1
 3. COLLECTOR 1
 4. EMITTER 1
 5. BASE 2
 6. COLLECTOR 2</p> | <p>STYLE 3:
 PIN 1. ENABLE
 2. N/C
 3. R BOOST
 4. Vz
 5. V in
 6. V out</p> | <p>STYLE 4:
 PIN 1. N/C
 2. V in
 3. NOT USED
 4. GROUND
 5. ENABLE
 6. LOAD</p> | <p>STYLE 5:
 PIN 1. EMITTER 2
 2. BASE 2
 3. COLLECTOR 1
 4. EMITTER 1
 5. BASE 1
 6. COLLECTOR 2</p> | <p>STYLE 6:
 PIN 1. COLLECTOR
 2. COLLECTOR
 3. BASE
 4. EMITTER
 5. COLLECTOR
 6. COLLECTOR</p> |
| <p>STYLE 7:
 PIN 1. COLLECTOR
 2. COLLECTOR
 3. BASE
 4. N/C
 5. COLLECTOR
 6. EMITTER</p> | <p>STYLE 8:
 PIN 1. Vbus
 2. D(in)
 3. D(in)+
 4. D(out)+
 5. D(out)
 6. GND</p> | <p>STYLE 9:
 PIN 1. LOW VOLTAGE GATE
 2. DRAIN
 3. SOURCE
 4. DRAIN
 5. DRAIN
 6. HIGH VOLTAGE GATE</p> | <p>STYLE 10:
 PIN 1. D(OUT)+
 2. GND
 3. D(OUT)-
 4. D(IN)-
 5. VBUS
 6. D(IN)+</p> | <p>STYLE 11:
 PIN 1. SOURCE 1
 2. DRAIN 2
 3. DRAIN 2
 4. SOURCE 2
 5. GATE 1
 6. DRAIN 1/GATE 2</p> | <p>STYLE 12:
 PIN 1. I/O
 2. GROUND
 3. I/O
 4. I/O
 5. VCC
 6. I/O</p> |
| <p>STYLE 13:
 PIN 1. GATE 1
 2. SOURCE 2
 3. GATE 2
 4. DRAIN 2
 5. SOURCE 1
 6. DRAIN 1</p> | <p>STYLE 14:
 PIN 1. ANODE
 2. SOURCE
 3. GATE
 4. CATHODE/DRAIN
 5. CATHODE/DRAIN
 6. CATHODE/DRAIN</p> | <p>STYLE 15:
 PIN 1. ANODE
 2. SOURCE
 3. GATE
 4. DRAIN
 5. N/C
 6. CATHODE</p> | <p>STYLE 16:
 PIN 1. ANODE/CATHODE
 2. BASE
 3. EMITTER
 4. COLLECTOR
 5. ANODE
 6. CATHODE</p> | <p>STYLE 17:
 PIN 1. EMITTER
 2. BASE
 3. ANODE/CATHODE
 4. ANODE
 5. CATHODE
 6. COLLECTOR</p> | |

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